

JC17 Rec'd PCT/PTO 07 JUN 2005

ALTERNATIVE TO PTO/SB/08a/b (06-03)

Substitute for form 1449/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(Use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	To be assigned <b>10/537804</b>
				Filing Date	Concurrently herewith
				First Named Inventor	Robert DWILINSKI
				Art Unit	<del>Not yet assigned</del> <b>1792</b>
				Examiner Name	<del>Not yet assigned</del> <b>Hiteshew</b>
Sheet	1	of	1	Attorney Docket Number	204552035400

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1.	6,177,057-B1	1-23-2001	Purdy	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	MM-DD-YYYY			
	2.	JP-10-7496	1-13-1998		abstract	
	3.	WO-98/55671-A1	12-10-1998			✓
	4.	GB-2326160-A	12-16-1998			✓
	5.	FR-2796657-A	1-26-2001			✓
	6.	WO-02/101120-A	12-19-2002			✓

\*EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	7.	Douglas R. Ketchum et al. (2001) "Crystal Growth of Gallium Nitride in Supercritical Ammonia," Journal of Crystal Growth 222, pp. 431-434	
	8.	R. Dwiliski et al. (1998) "AMMONO Method of BN, AlN and GaN Synthesis and Crystal Growth," MRS Internet J. Nitride Semiconductor Res. 3(25), 4 pages	
	9.	Masaichi Yano et al. (1999) "Control of Nucleation Site and Growth Orientation of Bulk GaN Crystals," Jpn. J. Appl. Phys. 38, pp. L1121-L1123	

\*EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	/Felisa Hiteshew/	Date Considered	04/18/2008
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va-A1480 REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /F.H./